Nch 80V 100A Power MOSFET

V_{DSS}	80V
R _{DS(on)} (Max.)	5.3mΩ
I _D	±100A
P_D	89W

●Features

- 1) Low on resistance
- 2) High power package (TO263AB)
- 3) Pb-free plating; RoHS compliant
- 4) Halogen free
- 5) 100% Rg and UIS tested

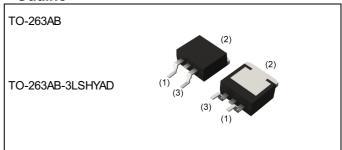
Application

Switching

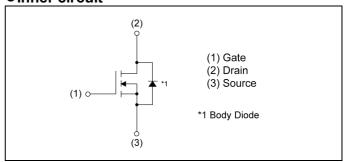
Motor drives

DC/DC converter

Outline



•Inner circuit



Packaging specifications

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	Packing	Embossed Tape		
	Reel size (mm)	330		
Туре	Tape width (mm)	24		
	Quantity (pcs)	800		
	Taping code	TL1		
	Marking	RJ1N04BBH		

● **Absolute maximum ratings** (T_a = 25°C ,unless otherwise specified)

Para	meter	Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	80	V
Continuous dusin summent	Silicon limit (V _{GS} =10V)	I _D *1	±100	А
Continuous drain current	$T_c = 25^{\circ}C (V_{GS} = 10V)$	I _D *2	±40	А
Pulsed drain current		I _{DP} *3	±400	Α
Gate - Source voltage		V_{GSS}	±20	V
Avalanche current, single pulse		l _{AS} *4	23	Α
Avalanche energy, single pulse		E _{AS} *4	42	mJ
Power dissipation		P _D *2	89	W
Junction temperature		T _j	150	°C
Operating junction and storage temperature range		T _{stg}	-55 to +150	°C

Thermal resistance

Parameter	Cymahal	Values			1.1-24
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	R _{thJC} *2	-	-	1.4	°C/W

● Electrical characteristics (T_a = 25°C)

Doromotor	Sumb of	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$ $V_{GS} = 0V, I_D = 1mA$		80	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$	$\frac{\Delta V_{(BR)DSS}}{\Delta T_i} I_D = 1 \text{mA}$ referenced to 25°C		58	-	mV/°C
Zero gate voltage drain current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0V	-	-	5	μA
Gate - Source leakage current	I _{GSS}	I_{GSS} $V_{GS} = \pm 20V, V_{DS} = 0V$		-	±500	nA
Gate threshold voltage	V _{GS(th)}	$V_{GS(th)}$ $V_{DS} = V_{GS}$, $I_D = 1mA$		-	4.0	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	I _D = 1mA referenced to 25°C	-	-5.0	-	mV/°C
Static drain - source	D *5	V _{GS} = 10V, I _D = 40A	-	4.4	5.3	m0
on - state resistance	R _{DS(on)} *5	V _{GS} = 6V, I _D = 20A	-	5.3	7.4	mΩ
Gate resistance	R _G	-	-	1.0	-	Ω
Forward Transfer Admittance	Y _{fs} *5	V _{DS} = 5V, I _D = 20A	20	-	-	S

^{*1} Limited by silicon chip capability.

^{*2} T_c =25°C, Limited only by maximum temperature allowed.

^{*3} Pw \leq 10µs, Duty cycle \leq 1%

^{*4} L \simeq 0.1mH, V_{DD} = 40V, R_G = 25 Ω , Starting T_j = 25 $^{\circ}$ C Fig.3-1,3-2

^{*5} Pulsed

● Electrical characteristics (T_a = 25°C)

Dorameter	Cumbal	Conditions		Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input capacitance	C _{iss}	V _{GS} = 0V	-	3280	-	
Output capacitance	C _{oss}	V _{DS} = 40V	-	730	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	1	23	1	
Turn - on delay time	t _{d(on)} *5	V _{DD} ≈ 40V,V _{GS} = 10V	1	30	1	
Rise time	t _r *5	I _D = 20A	-	14	-	
Turn - off delay time	t _{d(off)} *5	$R_L \simeq 2.0\Omega$	-	65	-	ns
Fall time	t _f *5	$R_G = 10\Omega$	-	38	-	

• Gate charge characteristics $(T_a = 25^{\circ}C)$

Daramatar	Cymahal	Conditions		Values			1.154	
Parameter	Symbol			Min.	Тур.	Max.	Unit	
Total gate charge	O *5	O *5		V _{GS} = 10V	-	46.0	-	
Total gate charge	\mathbf{Q}_{g}^{g}	Q_g^{*5} $V_{DD} \simeq 40V$		-	28.0	-	~ C	
Gate - Source charge	Q _{gs} *5	I _D = 40A	V _{GS} = 6V	-	10.4	-	nC	
Gate - Drain charge	Q _{gd} *5			-	7.1	-		

● Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions		Unit		
	Symbol	Conditions	Min.	Тур.	Max.	Offic
Continuous forward current	I _S *2		1	-	40	Α
Pulse forward current	I _{SP} *3	-	1	-	400	Α
Forward voltage	V _{SD} *5	V _{GS} = 0V, I _S = 40A	-	-	1.5	V
Reverse recovery time	t _{rr} *5	I _S = 40A, V _{GS} =0V	-	53	-	ns
Reverse recovery charge	Q _{rr} *5	di/dt = 100A/μs	-	52	-	nC

• Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

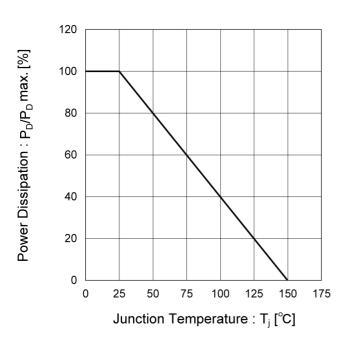
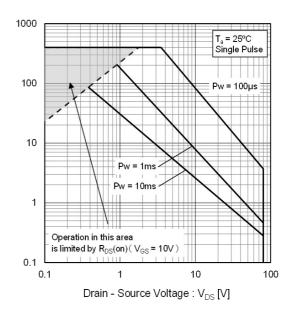


Fig.2 Maximum Safe Operating Area



Drain Current : I_D [A]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

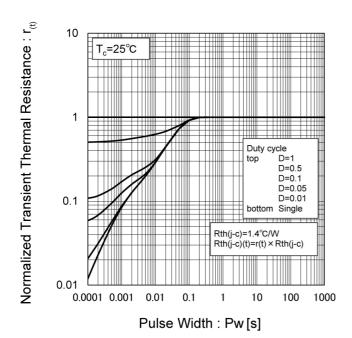
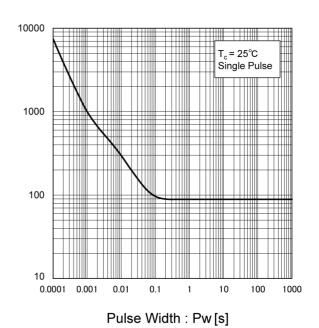


Fig.4 Single Pulse Maximum Power Dissipation



Peak Transient Power: P(W)

Drain Current : I_D [A]

Normalized Breakdown Voltage : $V_{(BR)DSS}$

• Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)

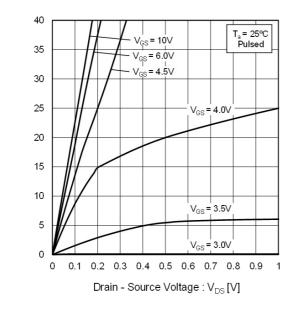


Fig.6 Typical Output Characteristics(II)

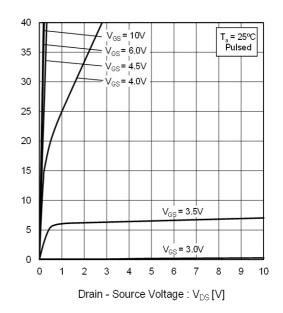


Fig.7 Normalized Breakdown Voltage vs. Junction Temperature

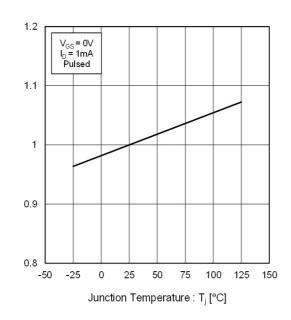
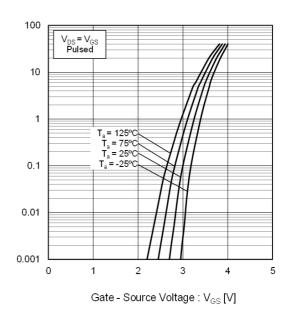


Fig.8 Typical Transfer Characteristics



Drain Current: I_D [A]

Drain Current : I_D [A]

Gate Threshold Voltage : $V_{GS(th)}[V]$

• Electrical characteristic curves

Fig.9 Gate Threshold Voltage vs.
Junction Temperature

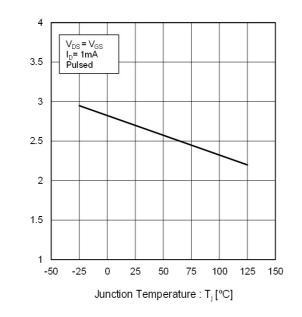


Fig.10 Forward Transfer Admittance vs.
Drain Current

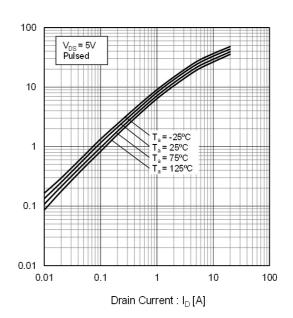


Fig.11 Drain Current Derating Curve

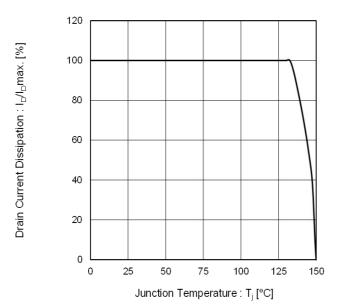
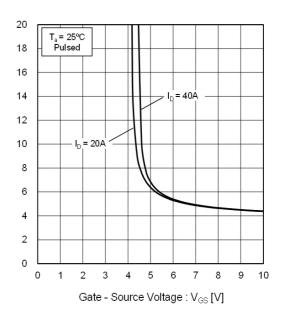


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Static Drain - Source On-State Resistance : $R_{\text{DS}(on)}\left[\text{m}\Omega\right]$

Forward Transfer Admittance : Y_{fs} [S]

• Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

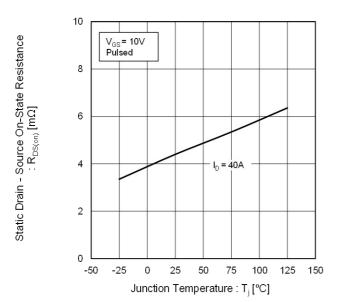
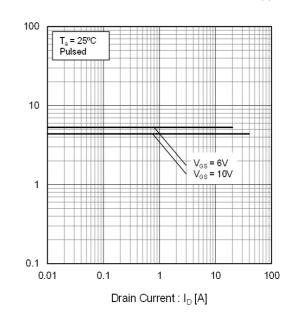


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (I)



Static Drain - Source On-State Resistance : $R_{\mathrm{DS(on)}}\left[m\Omega\right]$

Static Drain - Source On-State Resistance : $R_{\mathrm{DS(on)}} \left[m\Omega \right]$

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (II)

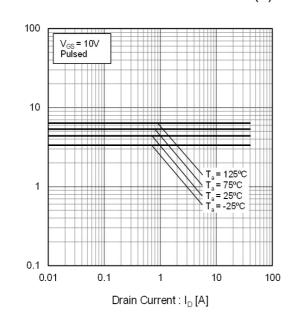
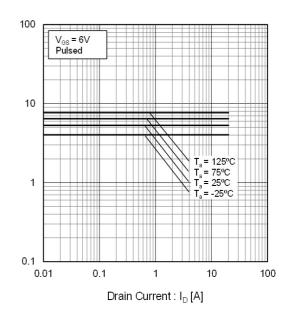


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current (III)



Static Drain - Source On-State Resistance

 $:R_{DS(on)}\left[m\Omega \right]$

Capacitance : C [pF]

Gate - Source Voltage : V_{GS} [V]

• Electrical characteristic curves

Fig.17 Typical Capacitances vs.

Drain - Source Voltage

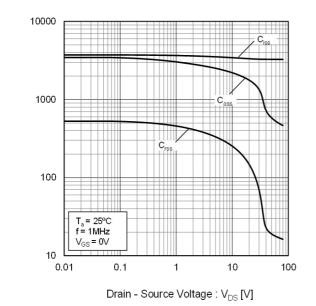


Fig.18 Switching Characteristics

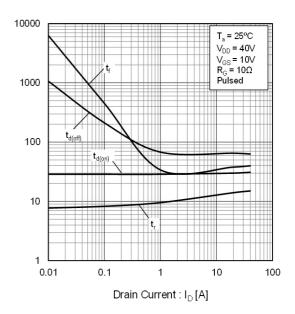


Fig.19 Typical Gate Charge

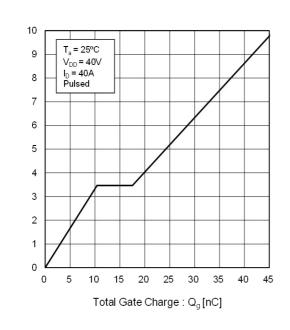
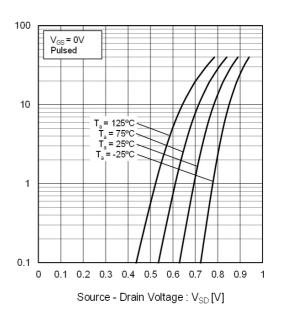


Fig.20 Source Current vs.

Source Drain Voltage



Source Current : I_s [A]

Switching Time: t [ns]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

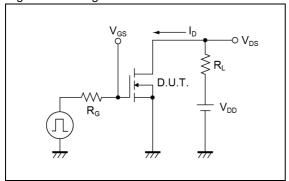


Fig.1-2 Switching Waveforms

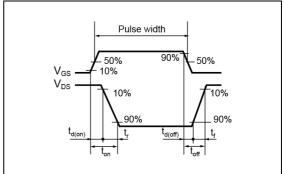


Fig.2-1 Gate Charge Measurement Circuit

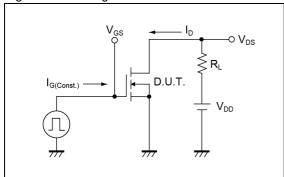


Fig.2-2 Gate Charge Waveform

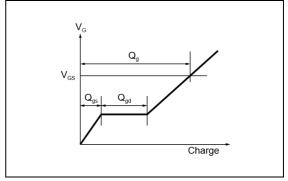


Fig.3-1 Avalanche Measurement Circuit

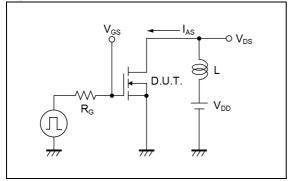
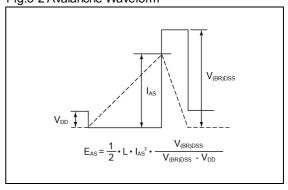
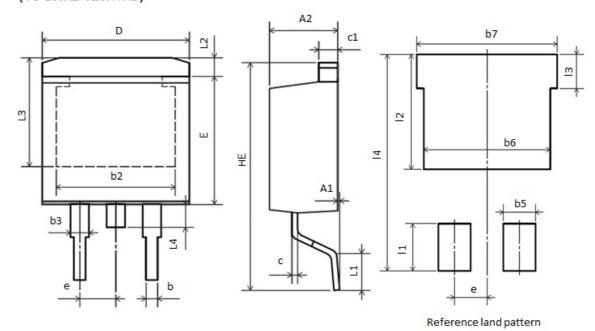


Fig.3-2 Avalanche Waveform



Dimensions

TO-263AB (TO-263AB-3LSHYAD)



DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
A1	0.00	0.25	0.000	0.010
A2	4.37	4.77	0.168	0.188
b	0.70	0.96	0.028	0.038
b2	7.50	7.2	0.295	_
b3	1.17	1.47	0.046	0.058
С	0.30	0.53	0.012	0.021
c1	1.22	1.42	0.048	0.056
D	9.86	10.36	0.388	0.408
Е	8.50	8.90	0.335	0.350
е	2.54		0.1	00
HE	14.70	15.50	0.579	0.610
L1	2.00	2.60	0.079	0.102
L2	1.07	1.47	0.042	0.058
L3	6.60	3.75	0.260	857
L4	1.40	1.70	0.055	0.067

DIM	MILIMETERS	INCHES
DIM	NOM	NOM
1	3.5	0.14
12	8.5	0.33
13	2.5	0.10
4	16.0	0.63
b5	2.5	0.10
Ь6	10.0	0.39
b7	11.0	0.43

Dimension in mm / inches



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JÁPAN	USA	EU	CHINA
CLASSⅢ	CL ACCIII	CLASS II b	CL ACCIII
CLASSIV	CLASSⅢ	CLASSⅢ	CLASSⅢ

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 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
 may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
 exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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